BYV29FX-600

Enhanced ultrafast rectifier diode

Rev. 01 — 30 June 2009 Product data sheet

1. Product profile

1.1 General description

Enhanced ultrafast epitaxial rectifier diode in a SOD113 (2-lead TO-220F) plastic package.

1.2 Features and benefits

- High thermal cycling performance
- Isolated package
- Low on-state losses
- Low thermal resistance
- Soft recovery characteristic

1.3 Applications

- Dual Mode (DCM and CCM) PFC
- Power factor Correction (PFC) for Interleaved Topology

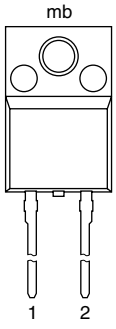
1.4 Quick reference data

Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	-	600	V
$I_{F(AV)}$	average forward current	square-wave pulse; δ = 0.5; T_h = 72 °C; see Figure 1; see Figure 2	-	-	9	A
Dynamic characteristics						
t_{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C; see Figure 5	-	17.5	35	ns
Static characteristics						
V_F	forward voltage	I_F = 9 A; T_j = 150 °C; see Figure 4	-	1.3	1.9	V

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	 SOD113 (TO-220F)	
2	A	anode		
mb	n.c.	mounting base; isolated		

3. Ordering information

Table 3. Ordering information

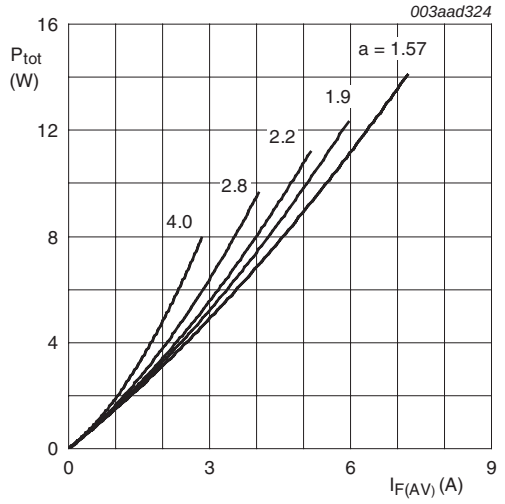
Type number	Package		
	Name	Description	Version
BYV29FX-600	TO-220F	plastic single-ended package; isolated heatsink mounted; 1 mounting hole; 2-lead TO-220 "full pack"	SOD113

4. Limiting values

Table 4. Limiting values

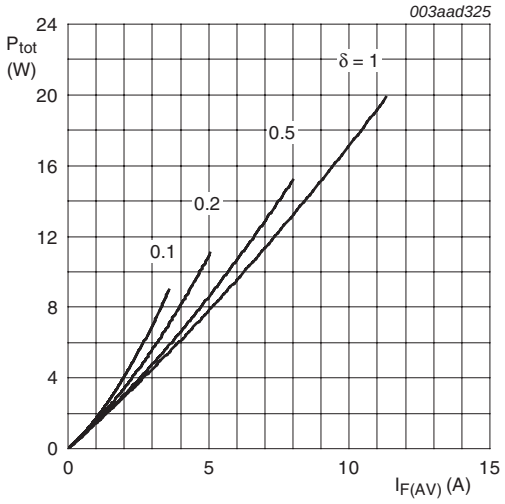
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{RRM}	repetitive peak reverse voltage		-	600	V
V_{RWM}	crest working reverse voltage		-	600	V
V_R	reverse voltage	DC	-	600	V
$I_{F(AV)}$	average forward current	square-wave pulse; δ = 0.5; T_h = 72 °C; see Figure 1; see Figure 2	-	9	A
I_{FRM}	repetitive peak forward current	square-wave pulse; δ = 0.5; t_p = 25 µs; T_h = 72 °C	-	18	A
I_{FSM}	non-repetitive peak forward current	t_p = 10 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	91	A
		t_p = 8.3 ms; sine-wave pulse; $T_{j(init)}$ = 25 °C	-	100	A



$a = \text{form factor} = I_{F(RMS)} / I_{F(AV)}$

Fig 1. Forward power dissipation as a function of average forward current; sinusoidal waveform; maximum values



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

Fig 2. Forward power dissipation as a function of average forward current; square waveform; maximum values

5. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-h)}$	thermal resistance from junction to heatsink	with heatsink compound; see Figure 3	-	-	5.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air		-	55	-	K/W

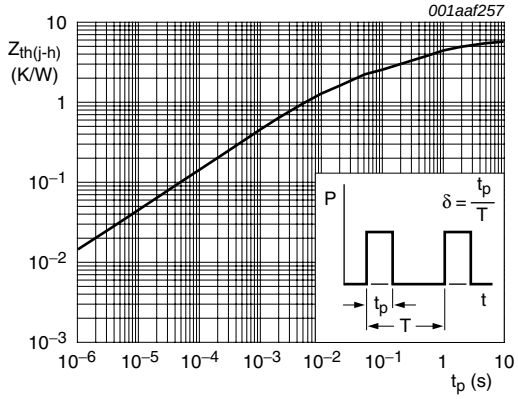


Fig 3. Transient thermal impedance from junction to heatsink as a function of pulse width

6. Isolation characteristics

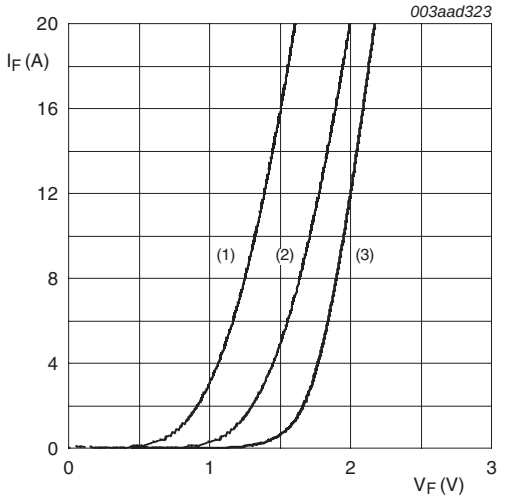
Table 6. Isolation characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{isol(RMS)}$	RMS isolation voltage	f = 1 MHz; RH = 65 %; between all pins and external heatsink	-	-	2500	V
C_{isol}	isolation capacitance	from cathode to external heatsink; f = 1 MHz	-	10	-	pF

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V_F	forward voltage	I_F = 9 A; T_j = 25 °C; see Figure 4	-	1.4	2.1	V
		I_F = 9 A; T_j = 150 °C; see Figure 4	-	1.3	1.9	V
I_R	reverse current	V_R = 600 V; T_j = 150 °C	-	-	1.5	mA
		V_R = 600 V; T_j = 25 °C	-	-	50	µA
Dynamic characteristics						
Q_r	recovered charge	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; see Figure 5	-	13	-	nC
t_{rr}	reverse recovery time	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; T_j = 25 °C; see Figure 5	-	17.5	35	ns
I_{RM}	peak reverse recovery current	I_F = 1 A; V_R = 30 V; dI_F/dt = 100 A/µs; see Figure 5	-	1.5	-	A
V_{FR}	forward recovery voltage	I_F = 1 A; dI_F/dt = 100 A/µs; see Figure 6	-	3.2	-	V



(1) $T_j = 150\ °C$; typical values
(2) $T_j = 150\ °C$; maximum values
(3) $T_j = 25\ °C$; maximum values

Fig 4. Forward current as a function of forward voltage

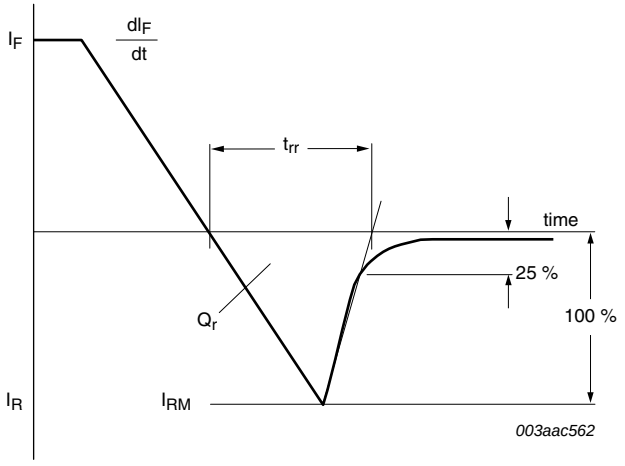


Fig 5. Reverse recovery definitions; ramp recovery

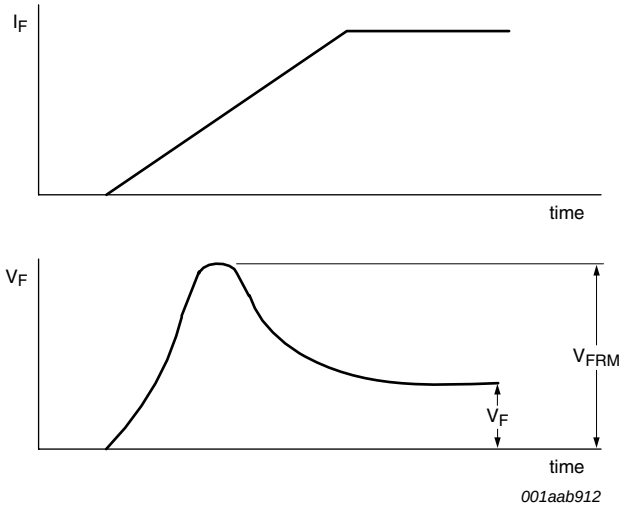
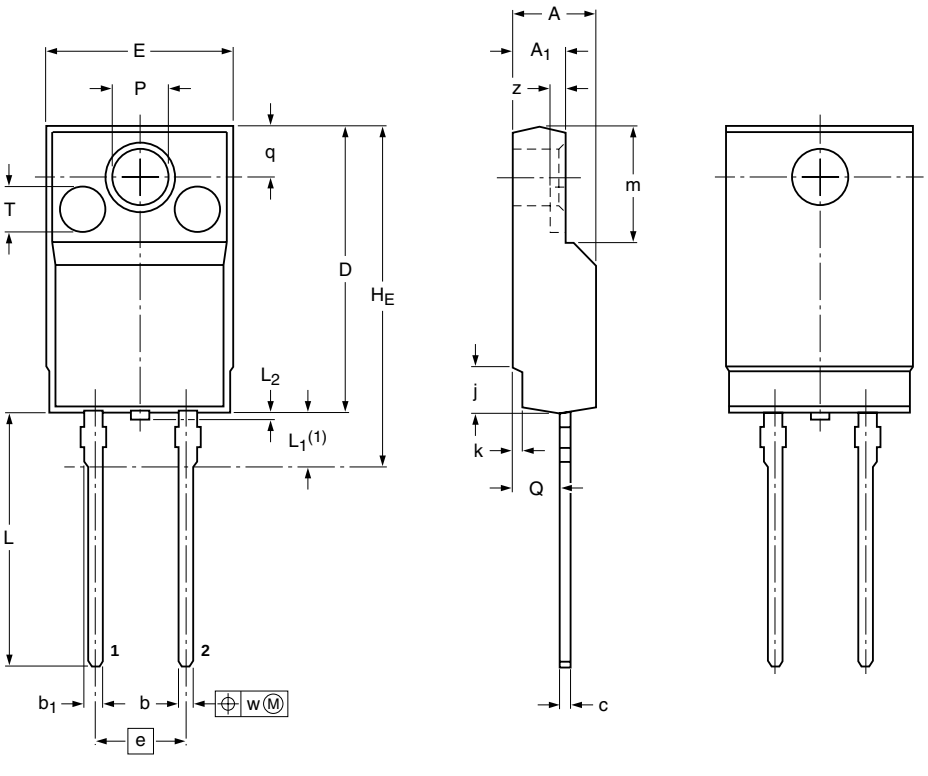


Fig 6. Forward recovery definitions

8. Package outline

Plastic single-ended package; isolated heatsink mounted;
1 mounting hole; 2-lead TO-220 'full pack' **SOD113**



z(2)
0.8

DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1	b	b_1	c	D	E	e	H_E max	j	k	L	L_1(1)	L_2 max	m	P	Q	q	T	w
mm	4.6 4.0	2.9 2.5	0.9 0.7	1.1 0.9	0.7 0.4	15.8 15.2	10.3 9.7	5.08	19.0	2.7 1.7	0.6 0.4	14.4 13.5	3.3 2.8	0.5	6.5 6.3	3.2 3.0	2.6 2.3	2.6	2.55	0.4

Notes

1. Terminals are uncontrolled within zone L_1.
2. z is depth of T.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD113		2-lead TO-220F				~~02-04-09~~ 07-06-18

Fig 7. Package outline SOD113 (TO-220F)

9. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BYV29FX-600_1	20090630	Product data sheet	-	-

10. Legal information

10.1 Data sheet status

Document status [1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

10.2 Definitions

Draft — The document is a draft version only. The content is still under internal review and subject to formal approval, which may result in modifications or additions. NXP Semiconductors does not give any representations or warranties as to the accuracy or completeness of information included herein and shall have no liability for the consequences of use of such information.

Short data sheet — A short data sheet is an extract from a full data sheet with the same product type number(s) and title. A short data sheet is intended for quick reference only and should not be relied upon to contain detailed and full information. For detailed and full information see the relevant full data sheet, which is available on request via the local NXP Semiconductors sales office. In case of any inconsistency or conflict with the short data sheet, the full data sheet shall prevail.

10.3 Disclaimers

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

10.4 Trademarks

Notice: All referenced brands, product names, service names and trademarks are the property of their respective owners.

11. Contact information

For more information, please visit: http://www.nxp.com

For sales office addresses, please send an email to: salesaddresses@nxp.com

12. Contents

For more information, please visit: http://www.nxp.com
For sales office addresses, please send an email to: salesaddresses@nxp.com

Date of release: 30 June 2009

Document identifier: BYV29FX-600_1